3/20/24

- Photo-diode
 - Reverse bias the junction (leakage current == dark current)
 - Light creates hole-electron pairs
 - h-e pairs immediately recombine in P+ and N regions
 - h-e pairs in the depletion region are swept to the P+ and N regions

• Holes \rightarrow V-, Electrons \rightarrow V+ \rightarrow increase in reverse current





- Photo-diode
 - Depletion region is not very large \rightarrow limited performance
 - PIN diode
 - Add an intrinsic region to increase the h-e generation volume



• Photo-diode

Material	Properties	Sensitivity	Usage
Silicon	low dark current, high speed	400 and 1000 nm	visible
Germanium	high dark current, slow speed	900 and 1600 nm	
Indium Gallium Arsenide Phosphide	low dark current, high speed	1000 and 1400 nm	infrared
Indium Gallium Arsenide	low dark current, high speed	900 and 1700 nm	

- Passive Pixel Sensor
 - Simple and small
 - Poor performance



Column (sense)

- Active Pixel Sensor (APS)
 - Reset fully charges the parasitic capacitance
 - Light discharges proportional to the intensity and length of exposure



- Active Pixel Sensor (APS)
 - 4T structure
 - Allows an electronic shutter (S/H)



Active Pixel Sensor (APS)



Active Pixel Sensor (APS)

Bayer Color Filter Mosaic Array and Underlying Photodiodes







Src: http://micro.magnet.fsu.edu/

Active Pixel Sensor (APS)



Active Pixel Sensor (APS)







Src: micron

Active Pixel Sensor (APS)



ELE 4142

© tj

Active Pixel Sensor (APS)

Dark Noise



- Active Pixel Sensor (APS)
 - Fixed Pattern Noise
 - Especially sensitive diodes



- Active Pixel Sensor (APS)
 - Banding Noise
 - Readout electronics patterns



120Mpixel Imager





Src: smarttechnologynow